

MC74HC132A

Quad 2-Input NAND Gate with Schmitt-Trigger Inputs High-Performance Silicon-Gate CMOS

The MC74HC132A is identical in pinout to the LS132. The device inputs are compatible with standard CMOS outputs; with pull-up resistors, they are compatible with LSTTL outputs.

The HC132A can be used to enhance noise immunity or to square up slowly changing waveforms.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2.0 to 6.0 V
- Low Input Current: 1.0 μ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 72 FETs or 18 Equivalent Gates

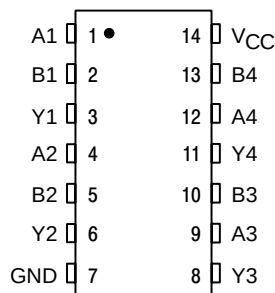


Figure 1. Pin Assignment

FUNCTION TABLE

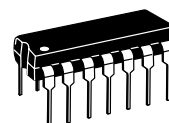
Inputs		Output
A	B	Y
L	L	H
L	H	H
H	L	H
H	H	L



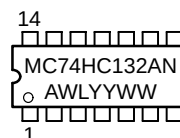
ON Semiconductor

<http://onsemi.com>

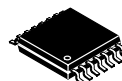
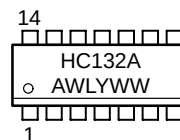
MARKING DIAGRAMS



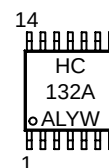
PDIP-14
N SUFFIX
CASE 646



SOIC-14
D SUFFIX
CASE 751A



TSSOP-14
DT SUFFIX
CASE 948G



A = Assembly Location
L, WL = Wafer Lot
Y, YY = Year
W, WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC74HC132AN	PDIP-14	2000/Box
MC74HC132AD	SOIC-14	55/Rail
MC74HC132ADR2	SOIC-14	2500/Reel
MC74HC132ADT	TSSOP-14	96/Rail
MC74HC132ADTR2	TSSOP-14	2500/Reel

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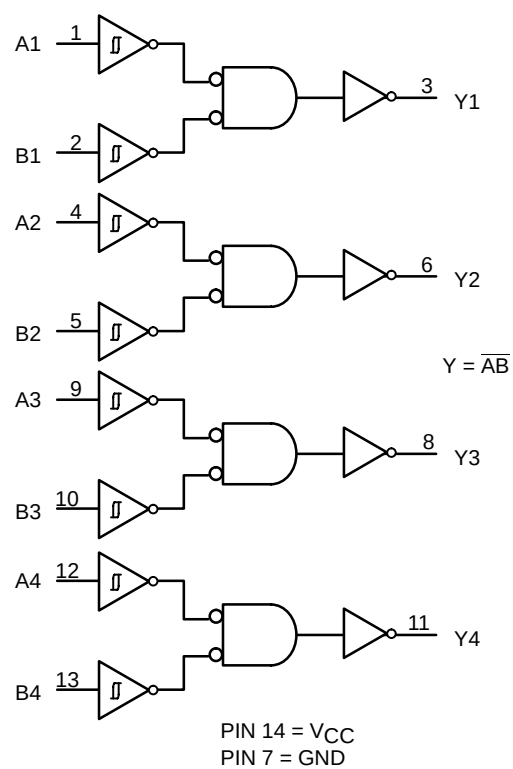


Figure 2. Logic Diagram

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MAXIMUM RATINGS (Note 1)

Symbol	Parameter	Value	Unit
V _{CC}	Positive DC Supply Voltage	− 0.5 to + 7.0	V
V _{IN}	Digital Input Voltage	− 0.5 to + 7.0	V
V _{OUT}	DC Output Voltage Output in 3-State High or Low State	− 0.5 to + 7.0 − 0.5 to V _{CC} + 0.5	V
I _{IK}	Input Diode Current	− 20	mA
I _{OK}	Output Diode Current	± 20	mA
I _{OUT}	DC Output Current, per Pin	± 25	mA
I _{CC}	DC Supply Current, V _{CC} and GND Pins	± 75	mA
I _{GND}	DC Ground Current per Ground Pin	± 75	mA
T _{STG}	Storage Temperature Range	− 65 to + 150	°C
T _L	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
T _J	Junction Temperature Under Bias	+ 150	°C
θ _{JA}	Thermal Resistance 14-PDIP 14-SOIC 14-TSSOP	78 125 170	°C/W
P _D	Power Dissipation in Still Air at 85°C PDIP SOIC TSSOP	750 500 450	mW
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 30% – 35%	UL–94–VO (0.125 in)	
V _{ESD}	ESD Withstand Voltage Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 100 > 500	V
I _{Latch-Up}	Latch-Up Performance Above V _{CC} and Below GND at 85°C (Note 5)	± 300	mA

1. Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Extended exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum-rated conditions is not implied.
2. Tested to EIA/JESD22–A114–A.
3. Tested to EIA/JESD22–A115–A.
4. Tested to JESD22–C101–A.
5. Tested to EIA/JESD78.
6. For high frequency or heavy load considerations, see Chapter 2the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V _{IN} , V _{OUT}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V _{CC}	V
T _A	Operating Temperature, All Package Types	− 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 3)	–	No Limit (Note 7)	ns

7. When V_{IN} ~ 0.5 V_{CC}, I_{CC} >> quiescent current.
8. Unused inputs may not be left open. All inputs must be tied to a high-logic voltage level or a low-logic input voltage level.

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DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V _{CC} V	Guaranteed Limit			Unit
				–55°C to 25°C	≤85°C	≤125°C	
V _{T+} max	Maximum Positive-Going Input Threshold Voltage (Figure 5)	V _{OUT} = 0.1 V I _{OUT} ≤ 20 μA	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	V
V _{T+} min	Minimum Positive-Going Input Threshold Voltage (Figure 5)	V _{OUT} = 0.1 V I _{OUT} ≤ 20 μA	2.0 4.5 6.0	1.0 2.3 3.0	0.95 2.25 2.95	0.95 2.25 2.95	V
V _{T–} max	Maximum Negative-Going Input Threshold Voltage (Figure 5)	V _{OUT} = V _{CC} – 0.1 V I _{OUT} ≤ 20 μA	2.0 4.5 6.0	0.9 2.0 2.6	0.95 2.05 2.65	0.95 2.05 2.65	V
V _{T–} min	Minimum Negative-Going Input Threshold Voltage (Figure 5)	V _{OUT} = V _{CC} – 0.1 V I _{OUT} ≤ 20 μA	2.0 4.5 6.0	0.3 0.9 1.2	0.3 0.9 1.2	0.3 0.9 1.2	V
V _H max (Note 9)	Maximum Hysteresis Voltage (Figure 5)	V _{OUT} = 0.1 V or V _{CC} – 0.1 V I _{OUT} ≤ 20 μA	2.0 4.5 6.0	1.2 2.25 3.0	1.2 2.25 3.0	1.2 2.25 3.0	V
V _H min (Note 9)	Minimum Hysteresis Voltage (Figure 5)	V _{OUT} = 0.1 V or V _{CC} – 0.1 V I _{OUT} ≤ 20 μA	2.0 4.5 6.0	0.2 0.4 0.5	0.2 0.4 0.5	0.2 0.4 0.5	V
V _{OH}	Minimum High-Level Output Voltage	V _{IN} ≤ V _{T–} min or V _{T+} max I _{OUT} ≤ 20 μA	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		V _{IN} ≤ –V _{T–} min or V _{T+} max I _{OUT} ≤ 4.0 mA I _{OUT} ≤ 5.2 mA	4.5 6.0	3.98 5.48	3.84 5.34	3.7 5.2	V
V _{OL}	Maximum Low-Level Output Voltage	V _{IN} ≥ V _{T+} max I _{OUT} ≤ 20 μA	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		V _{IN} ≥ V _{T+} max I _{OUT} ≤ 4.0 mA I _{OUT} ≤ 5.2 mA	4.5 6.0	0.26 0.26	0.33 0.33	0.4 0.4	V
I _{IN}	Maximum Input Leakage Current	V _{IN} = V _{CC} or GND	6.0	±0.1	±1.0	±1.0	μA
I _{CC}	Maximum Quiescent Supply Current (per Package)	V _{IN} = V _{CC} or GND I _{OUT} = 0 μA	6.0	1.0	10	40	μA

9. V_Hmin > (V_{T+}min) – (V_{T–}max); V_Hmax = (V_{T+}max) + (V_{T–}min).

10. Information on typical parametric values can be found in the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

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AC ELECTRICAL CHARACTERISTICS ($C_L = 50$ pF, Input $t_r = t_f = 6.0$ ns)

Symbol	Parameter	V _{CC} V	Guaranteed Limit			Unit
			−55°C to 25°C	≤85°C	≤125°C	
t_{PLH} , t_{PHL}	Maximum Propagation Delay, Input A or B to Output Y (Figures 3 and 4)	2.0 4.5 6.0	125 25 21	155 31 26	190 38 32	ns
t_{TLH} , t_{THL}	Maximum Output Transition Time, Any Output (Figures 3 and 4)	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns
C_{in}	Maximum Input Capacitance	—	10	10	10	pF

11. For propagation delays with loads other than 50 pF, and information on typical parametric values, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

C_{PD}	Power Dissipation Capacitance (per Gate) (Note 12)	Typical @ 25°C, V _{CC} = 5.0 V	pF
		24	

12. Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

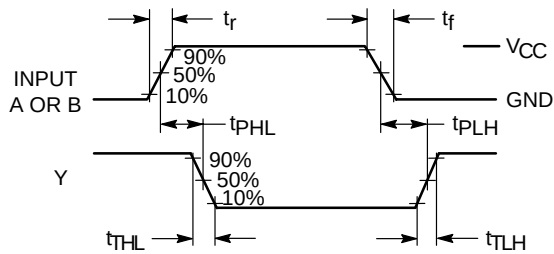
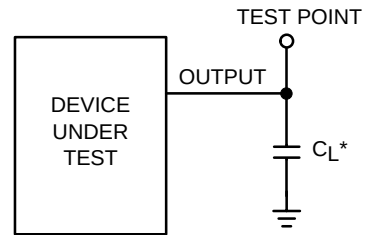


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance

Figure 4. Test Circuit

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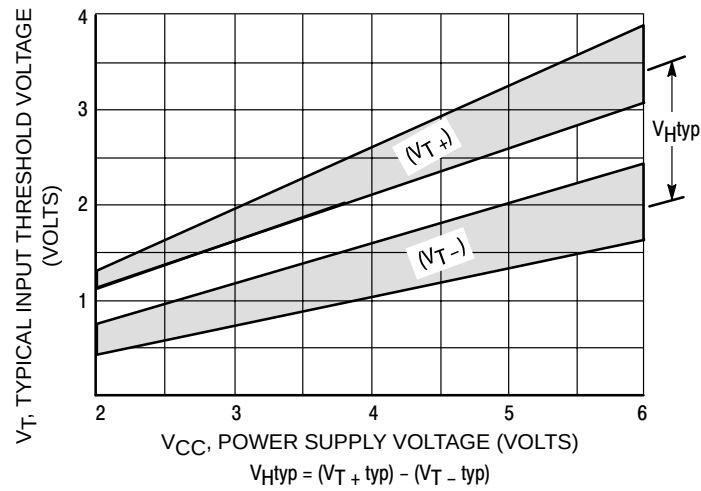


Figure 5. Typical Input Threshold, V_{T+} , V_{T-} Versus Power Supply Voltage

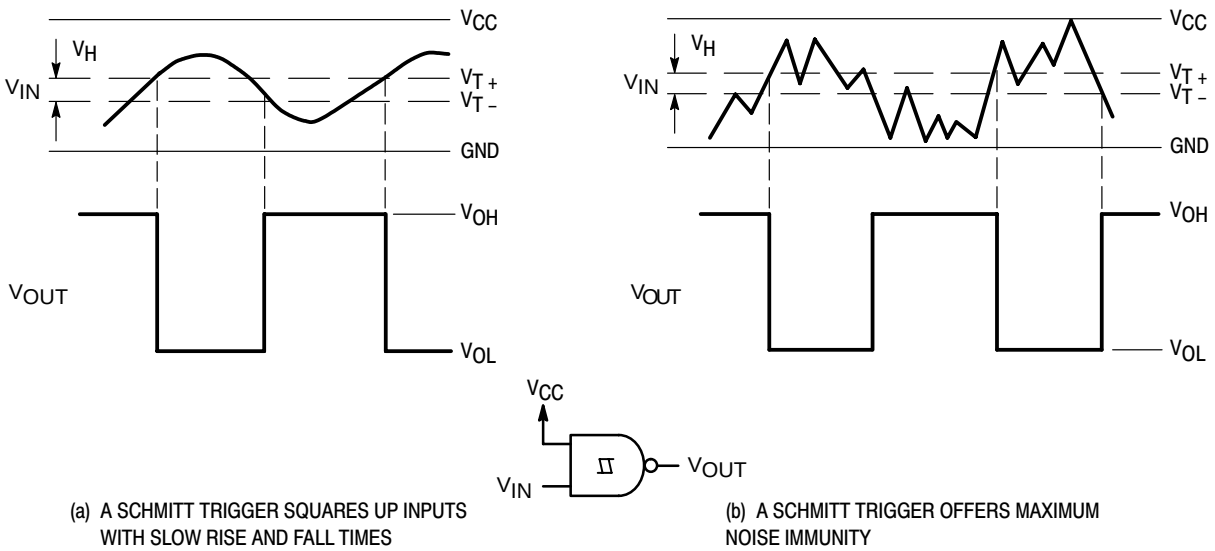
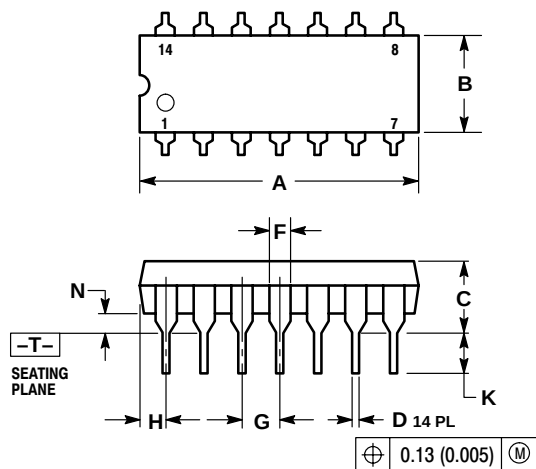


Figure 6. Typical Schmitt-Trigger Applications

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PACKAGE DIMENSIONS

PDIP-14
N SUFFIX
CASE 646-06
ISSUE M

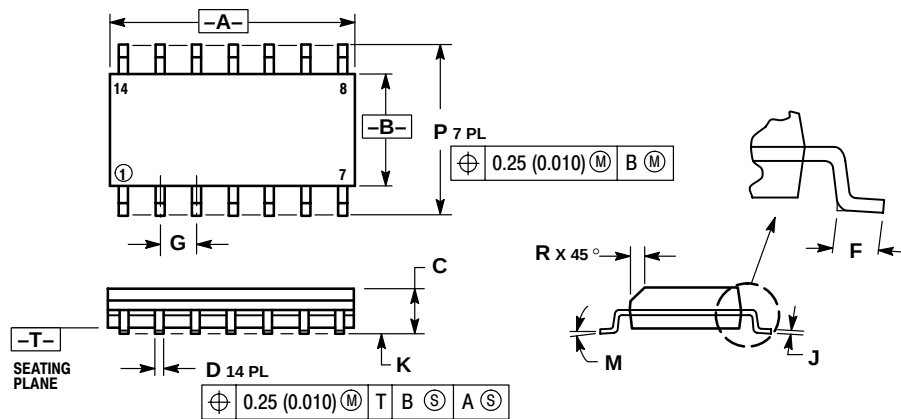


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.715	0.770	18.16	18.80
B	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
H	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
M	10°		10°	
N	0.015	0.039	0.38	1.01

SOIC-14
D SUFFIX
CASE 751A-03
ISSUE F



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

